

UTC M28S

NPN EPITAXIAL SILICON TRANSISTOR

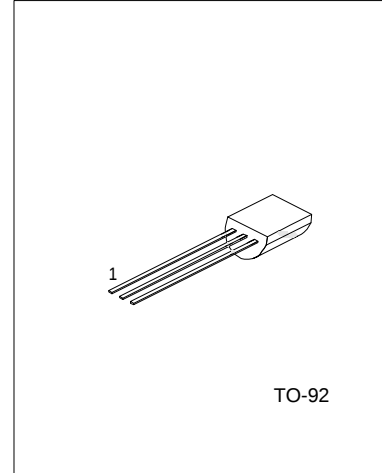
AUDIO OUTPUT DRIVER AMPLIFIER

FEATURES

- *Excellent HFE linearity
- *High DC Current Gain
- *High Power Dissipation

APPLICATION

- *Audio output driver amplifier
- *General purpose switch



1:EMITTER 2:COLLECTOR 3:BASE

ABSOLUTE MAXIMUM RATINGS (Ta=25°C, unless otherwise specified)

PARAMETERS	SYMBOL	RATING	UNITS
Collector-base voltage	V _{CB0}	40	V
Collector-emitter voltage	V _{CEO}	20	V
Emitter-base voltage	V _{EB0}	6	V
Collector dissipation(Ta=25°C)	P _c	850	mW
Collector current	I _c	1.25	A
Base current	I _B	0.4	A
Junction Temperature	T _j	150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS(Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-base voltage	V _{CB0}	I _c =0.1mA	40			V
Collector-emitter voltage	V _{CEO}	I _c =1mA	20			V
Emitter-base voltage	V _{EB0}	I _E =0.1mA	6			V
Collector cut-off current	I _{CBO}	V _{CB} =35V, I _E =0			100	nA
Emitter cut-off current	I _{EB0}	V _{EB} =5V, I _c =0			100	nA
DC current gain(note)	h _{FE1}	V _{CE} =1V, I _c =1mA	290		1000	
	h _{FE2}	V _{CE} =1V, I _c =0.1A	300			
	h _{FE3}	V _{CE1} =1V, I _c =0.3A	300			
	h _{FE4}	V _{CE} =1V, I _c =0.5A	300			
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =600mA, I _B =20mA			0.55	V
Current gain bandwidth product	f _T	V _{CE} =10V, I _c =50mA, f=1MHz	100			MHz
Output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz		9		pF

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CLASSIFICATION OF hFE2

RANK	B	C	D
RANGE	300-550	500-700	650-1000